

WHAT IS CLAIMED IS:

1. An electro-optical device, comprising, above a substrate:
scanning lines and data lines that intersect with each other to form a grid-like pattern;
thin-film transistors, each of the thin-film transistors being disposed in correspondence with intersections of one of the scanning lines and one of the data lines;
pixel electrodes respectively being disposed in correspondence with the thin-film transistors;
a first light shielding film laminated between the data line and the pixel electrode; and
a storage capacitor including the first light shielding film, laminated between the data line and the pixel electrode.
2. The electro-optical device according to claim 1, the thin-film transistor having a channel region which is formed in an intersection portion of the scanning line and the data line.
3. The electro-optical device according to claim 1, the storage capacitor comprising the first light shielding film and a capacitive electrode of pixel-electrode potential.
4. The electro-optical device according to claim 3, the capacitive electrode being electrically connected to a semiconductor layer of the thin film transistor via a barrier layer forming a film of the data line.
5. The electro-optical device according to claim 4, the barrier layer being formed along the data line and the scanning line.
6. The electro-optical device according to claim 1, the first light shielding film being formed along the data line and the scanning line.
7. The electro-optical device according to claim 6, the first light shielding film being formed in a grid configuration.
8. An electronic apparatus comprising an electro-optical device according to claim 1.